

Fig. 1

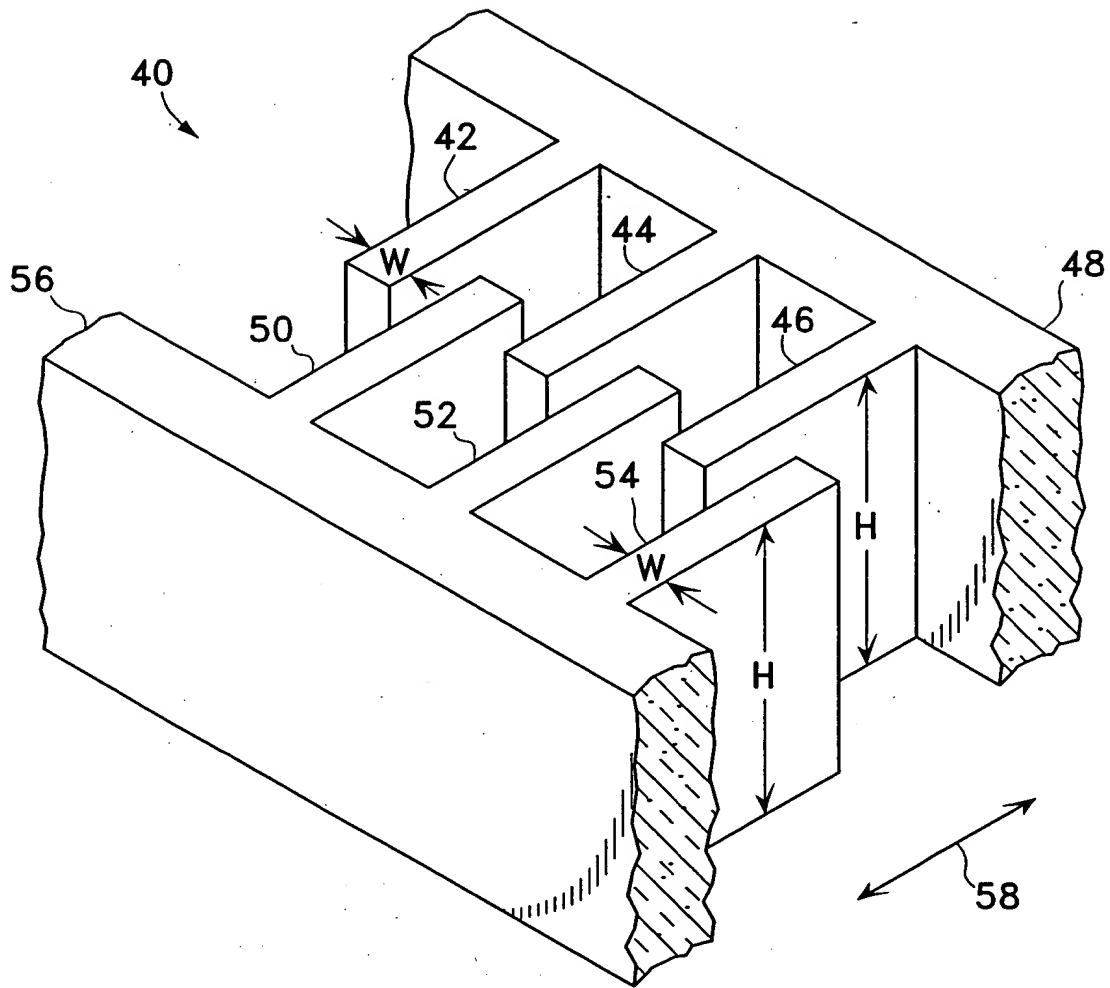


Fig. 2

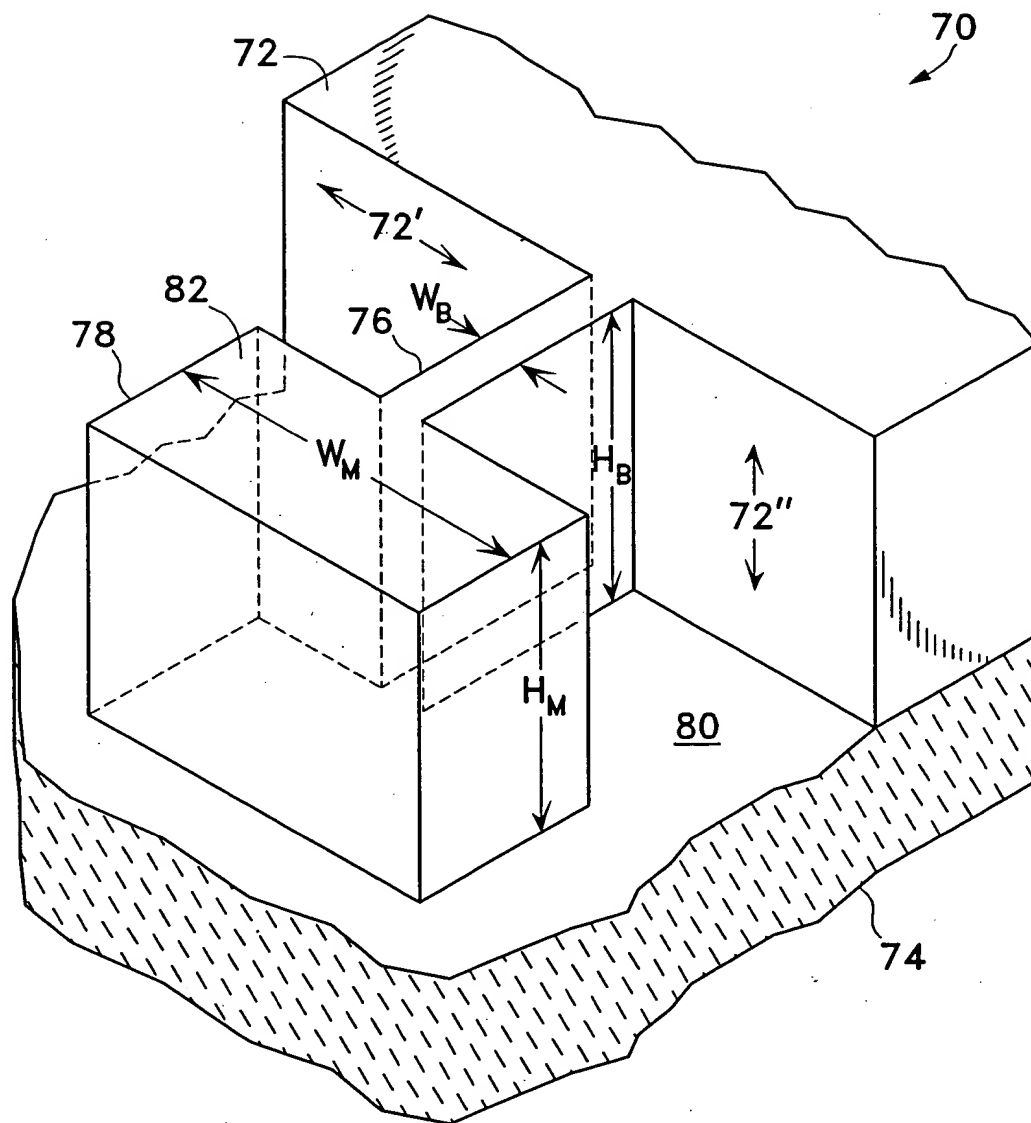


Fig. 3

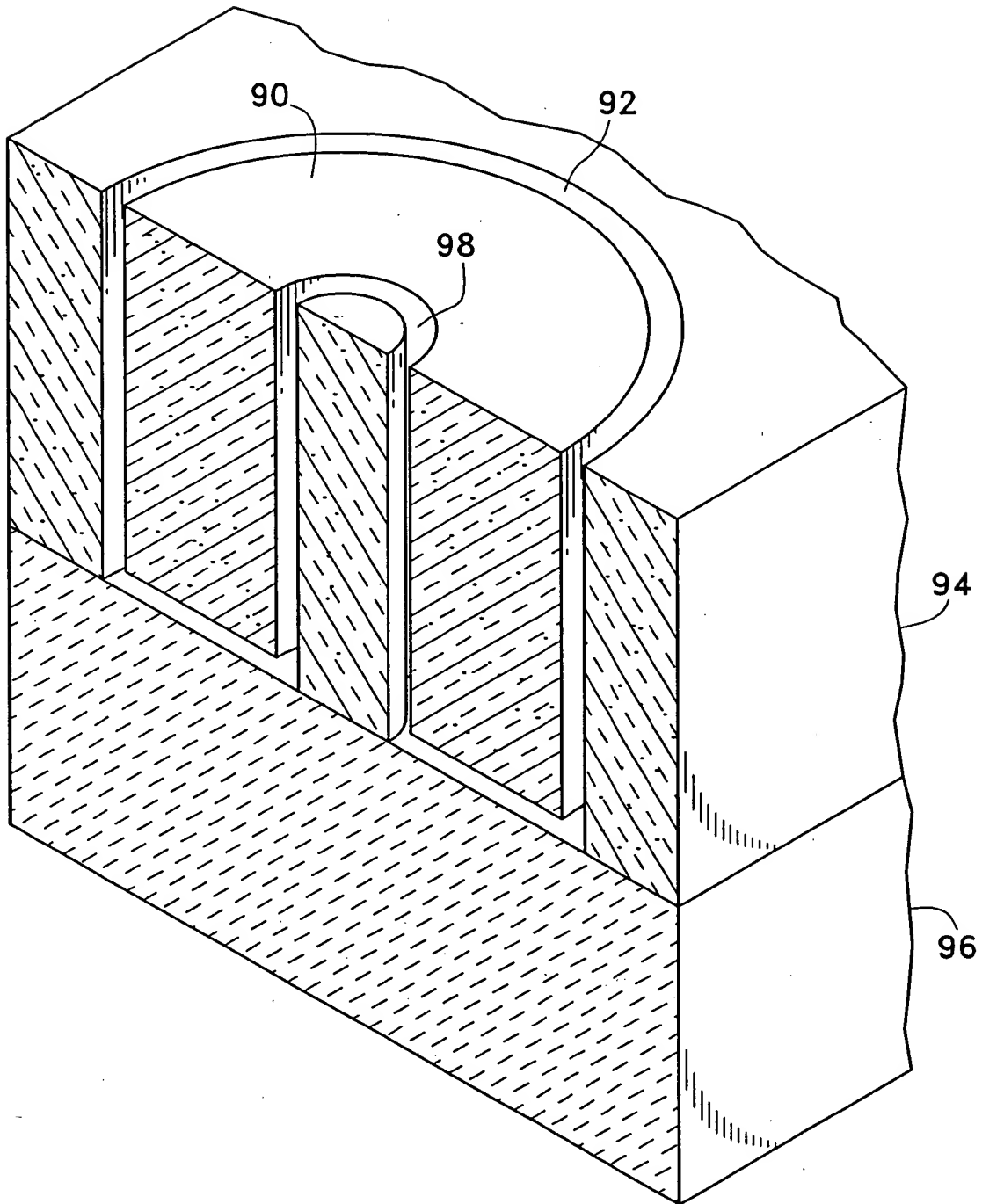


Fig. 4

0092814-00101
46T82660

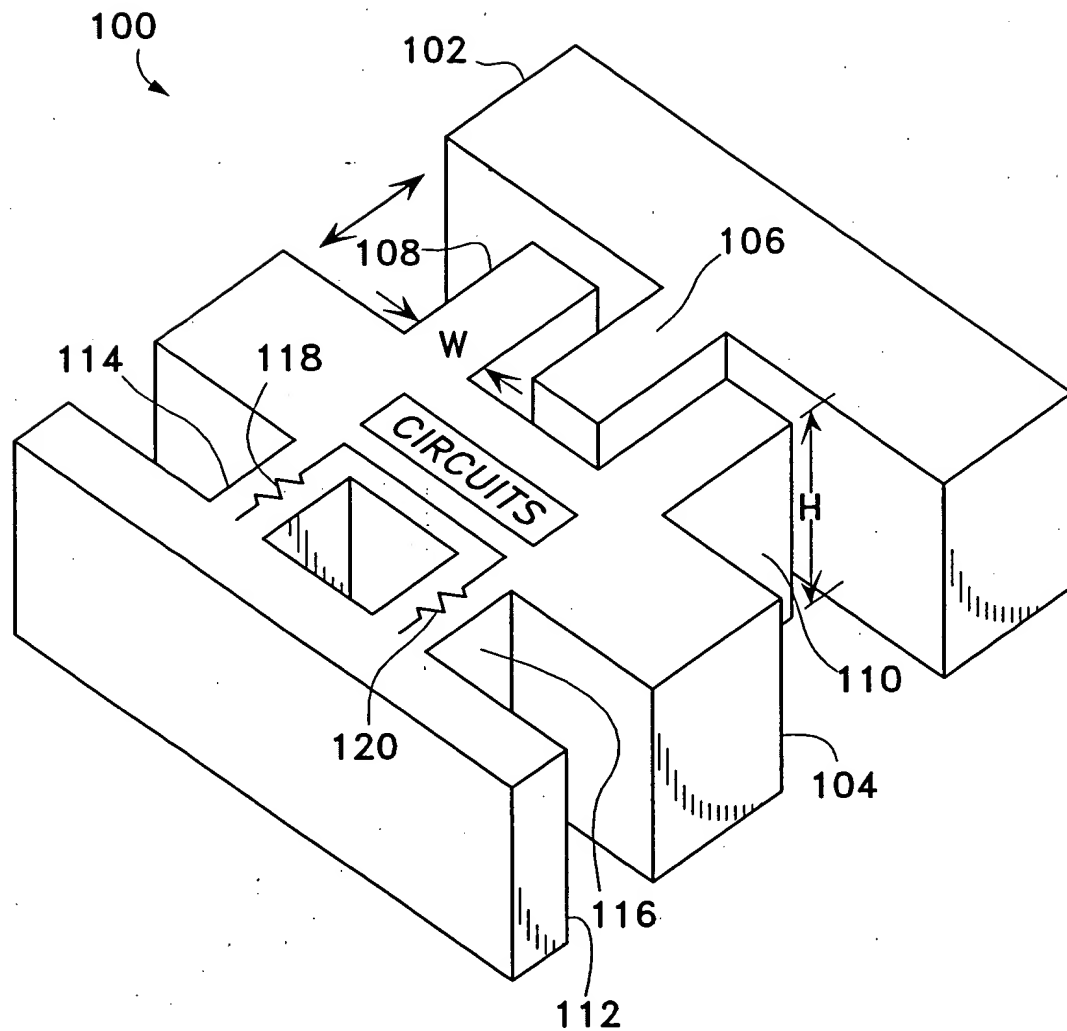


Fig. 5

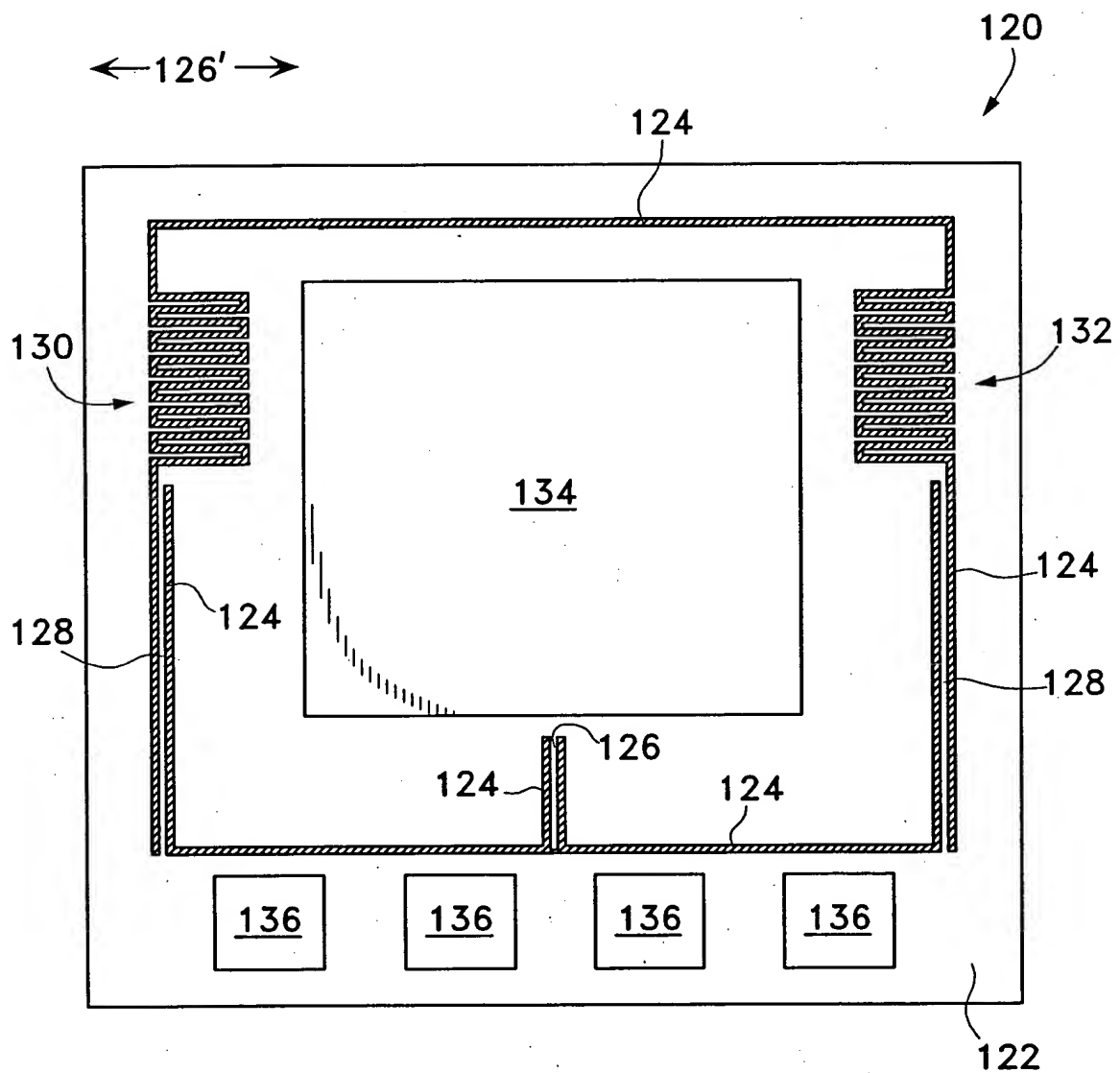


Fig. 6

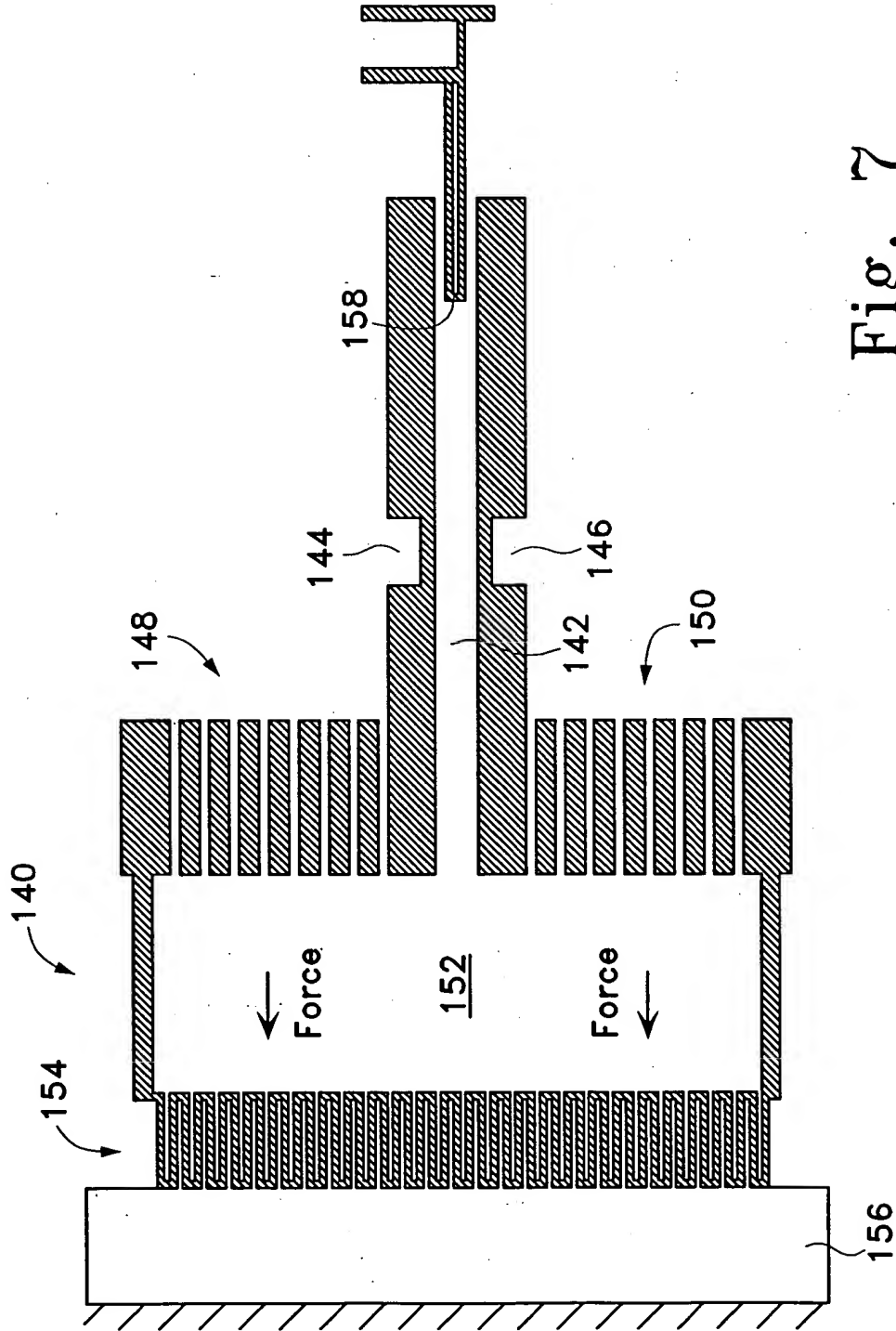


Fig. 7

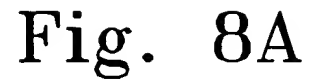


Fig. 8B

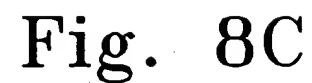
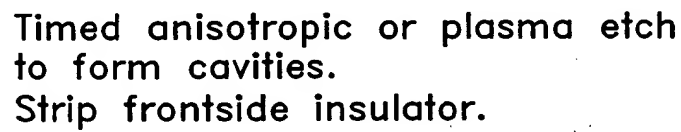


Fig. 8D



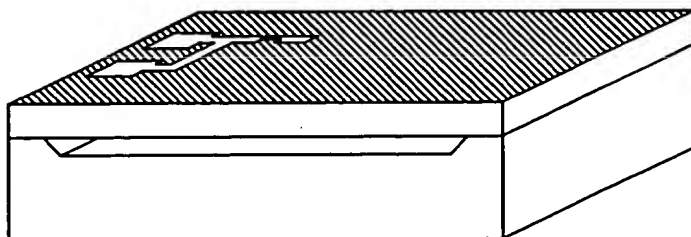


Fig. 8E

Deposit insulator on frontside and process sensing on chip circuits.

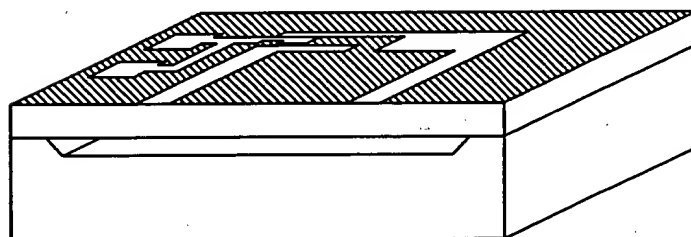


Fig. 8F

Define MEMS structure in insulator layer.

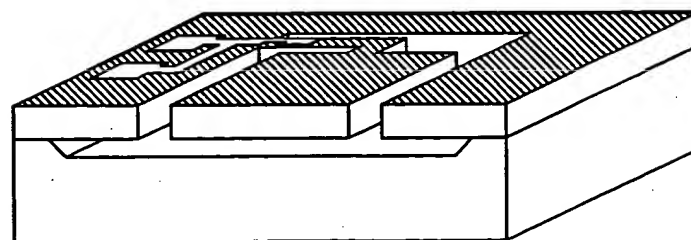


Fig. 8G

Anisotropic plasma etch to form MEMS structure.

09928194-081101

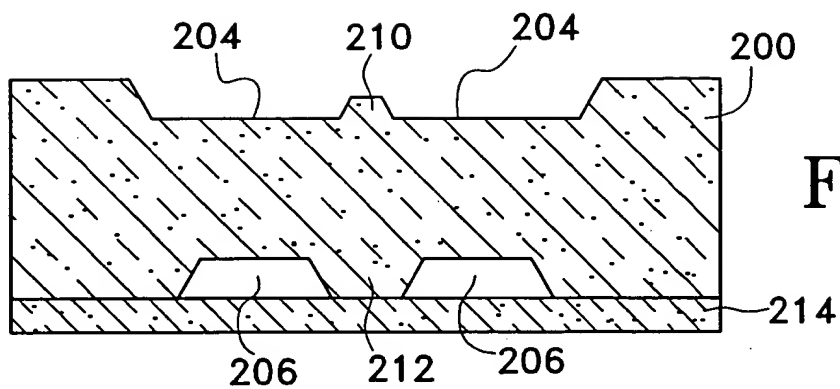


Fig. 9A

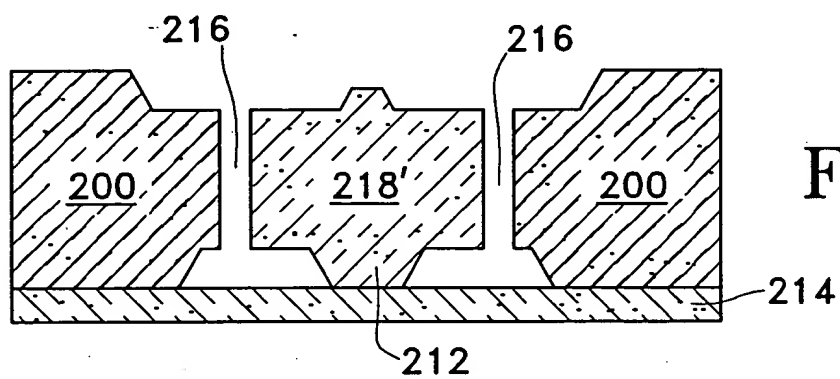


Fig. 9B

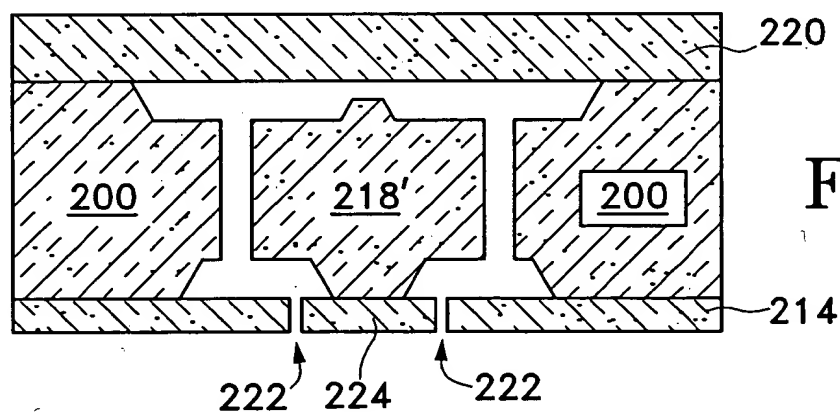


Fig. 9C

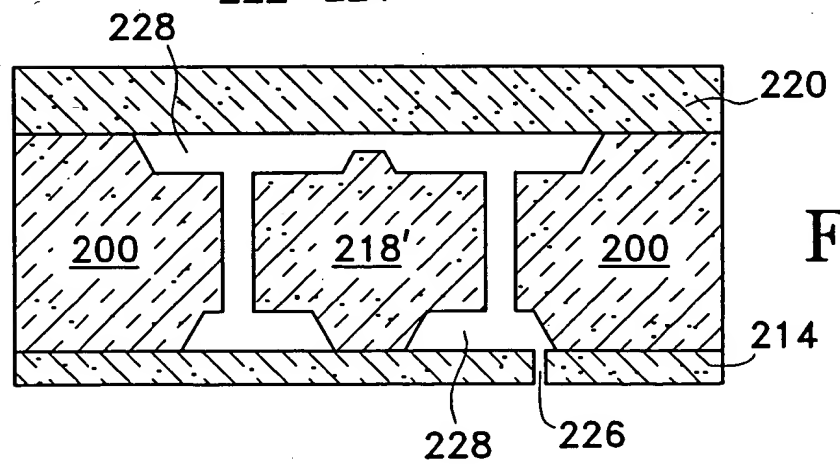


Fig. 9D

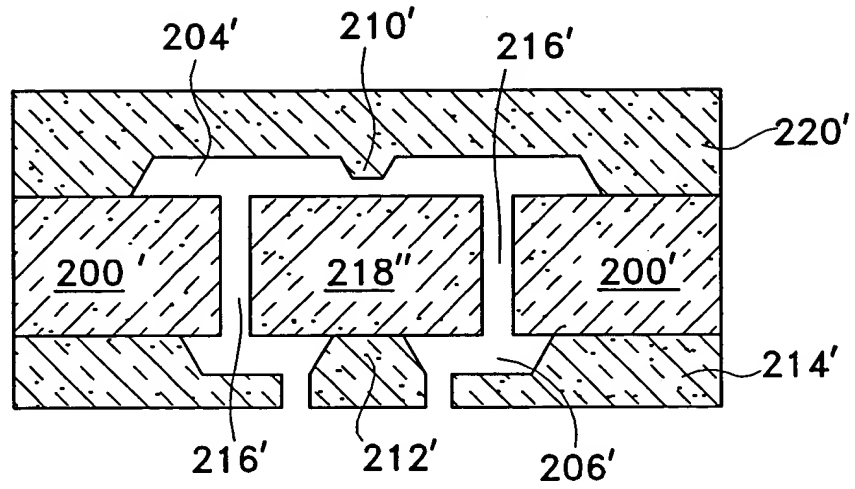


Fig. 10

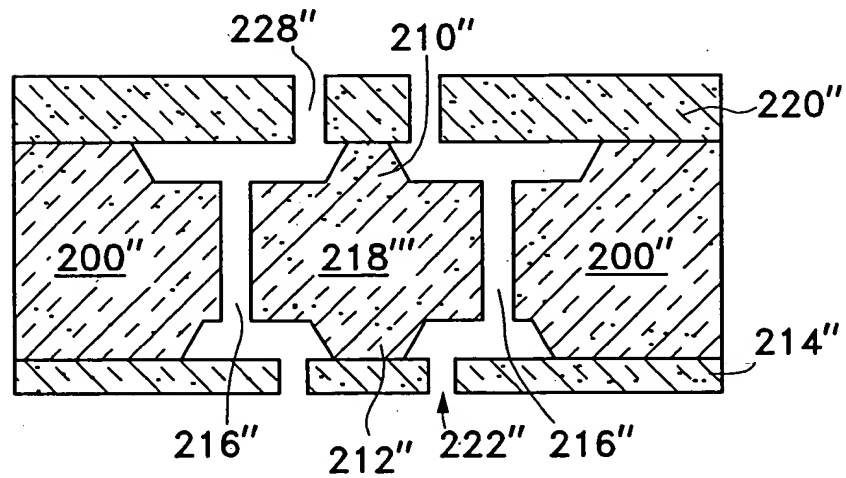


Fig. 11

09928194-081101

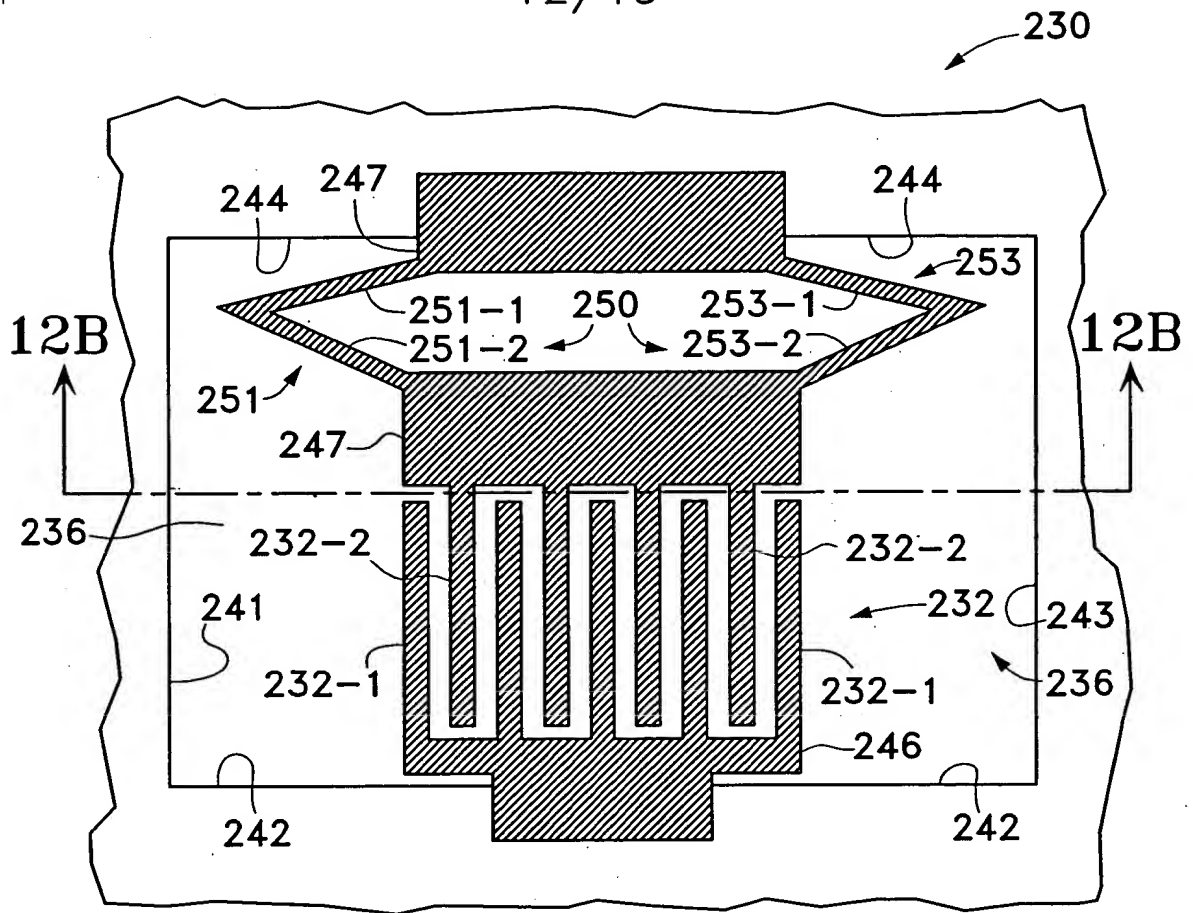


Fig. 12A

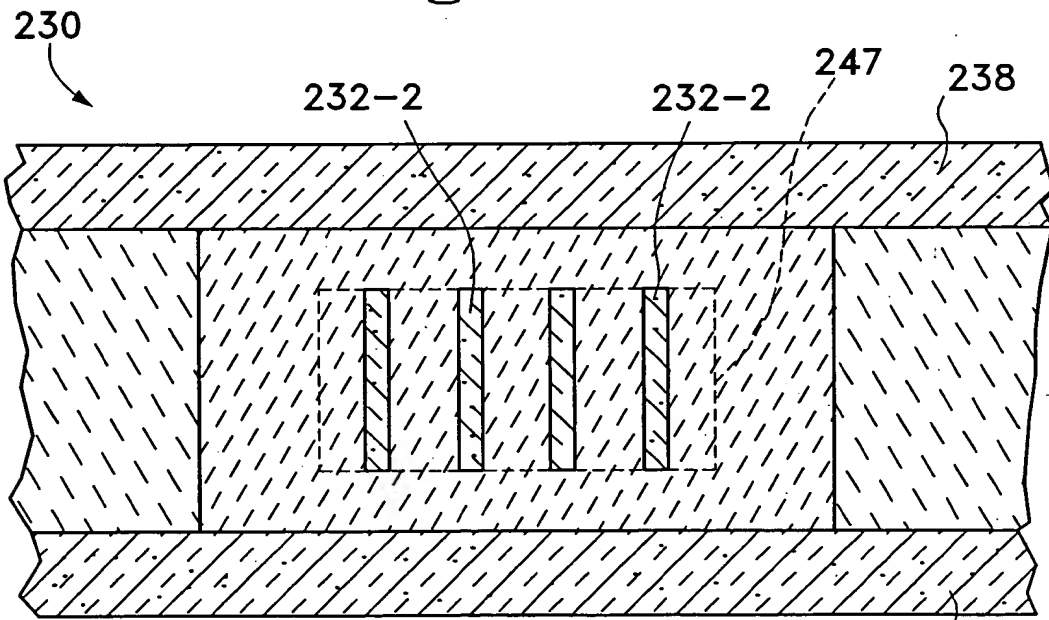


Fig. 12B

240

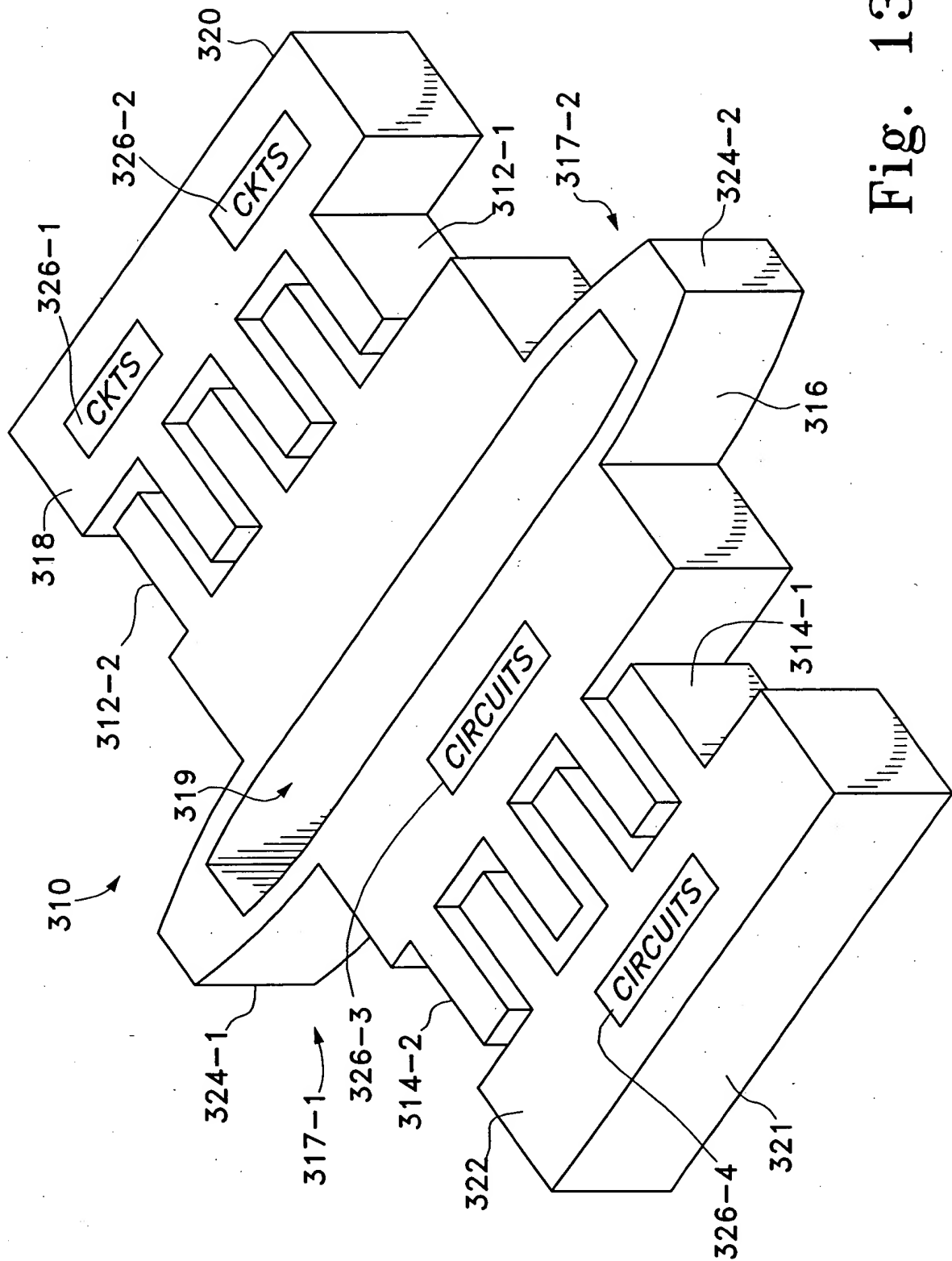


Fig. 13